ABSTRACT

There is provided an etching method capable of selective etching of an etching object over a non-etching object. The etching method includes an etching step of bringing an etching gas containing an etching compound into contact with a member to be etched (400) having an etching object (silicon material) and a non-etching object (carbon material) and selectively etching the etching object over the non-etching object. The etching compound is fluoro-dithiethane represented by Chemical Formula $C_xF_yS_2$, wherein, in Chemical Formula, x is 2 or more and 6 or less and y is 4 or more and 12 or less. The etching gas contains or does not contain at least one type of metal among sodium, magnesium, aluminum, potassium, calcium, chromium, manganese, iron, cobalt, nickel, copper, and molybdenum, and, when the at least one type of metal is contained, the total concentration of all types of the contained metals is 300 ppb by mass or less.

FIG. 1